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Form 1449 (Modified)	Atty Docket No.	Application No.:
	UNTYP022	10/680,508
Information Disclosure Statement By Applicant	Applicant: Rinerson, et al.	
	Filing Date	Group
(Use Several Sheets if Necessary)	October 6, 2003	~~2824~~ 2818

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A	5,287,326	02/15/94	Hirata	365	203.03	9/24/1992
	C	5,422,842	06/06/95	Cernea, et al.	365	185.22	7/8/1993
	D	5,495,442	02/27/96	Cernea, et al.	365	185.03	5/4/1995
	E	5,532,964	07/02/96	Cernea, et al.	365	189.09	5/4/1995
	F	6,204,139	03/20/01	Liu, et al.	438	385	8/25/1998
	G	6,574,145	06/03/03	Kleveland, et al.	365	185.19	6/29/2001

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	H	Beck, A. et al., "*Reproducible switching effect in thin oxide films for memory applications,*" Applied Physics Letters, Vol. 77, No. 1, 3 July 2000,139-141.
	I	Rossel, C. et al., "*Electrical current distribution across a metal-insulator-metal structure during bistable switching,*" Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
	J	Watanabe, Y. et al., "*Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped $SrTiO_3$ single crystals,*" Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.

Examiner	Date Considered
Luan Duong	11/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

OIPE JC64
FEB 27 2004
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Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	A	Liu, S.Q., et al., "*Electric-pulse-induced reversible resistance change effect in magnetoresistive films*", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
	B	Liu, S.Q., et al., "*A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films*", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.

Examiner	Date Considered
	11/04

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